

# FDMC7664

## N-Channel PowerTrench® MOSFET

30 V, 18.8 A, 4.2 mΩ

### Features

- Max  $r_{DS(on)}$  = 4.2 mΩ at  $V_{GS} = 10$  V,  $I_D = 18.8$  A
- Max  $r_{DS(on)}$  = 5.5 mΩ at  $V_{GS} = 4.5$  V,  $I_D = 16.1$  A
- High performance technology for extremely low  $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

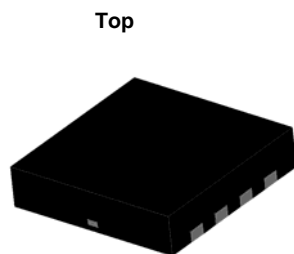


### General Description

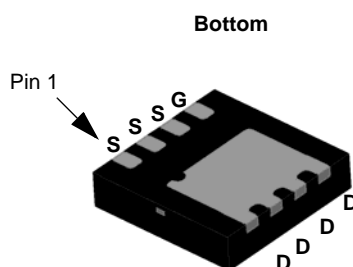
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

### Applications

- DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook

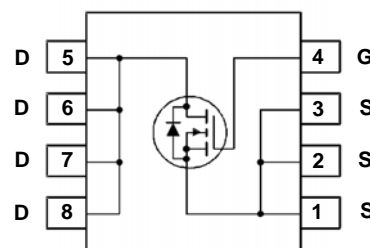


Top



Bottom

MLP 3.3x3.3



### MOSFET Maximum Ratings $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	30	V
$V_{GS}$	Gate to Source Voltage	±20	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25$ °C	24	A
	-Continuous $T_A = 25$ °C (Note 1a)	18.8	
	-Pulsed	60	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	188	mJ
$P_D$	Power Dissipation $T_C = 25$ °C	45	W
	Power Dissipation $T_A = 25$ °C (Note 1a)	2.3	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC7664	FDMC7664	MLP 3.3x3.3	13 "	12 mm	3000 units

**Electrical Characteristics**  $T_J = 25\text{ }^{\circ}\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		12		mV/ $^{\circ}\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$ , $V_{GS} = 0\text{ V}$ $T_J = 125\text{ }^{\circ}\text{C}$			1 250	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current, Forward	$V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$			100	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	1.0	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^{\circ}\text{C}$		-7		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 18.8\text{ A}$		3.6	4.2	m $\Omega$
		$V_{GS} = 4.5\text{ V}$ , $I_D = 16.1\text{ A}$		4.5	5.5	
		$V_{GS} = 10\text{ V}$ , $I_D = 18.8\text{ A}$ $T_J = 125\text{ }^{\circ}\text{C}$		4.4	5.4	
$g_{FS}$	Forward Transconductance	$V_{DD} = 5\text{ V}$ , $I_D = 18.8\text{ A}$		115		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}$ , $V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$		3655	4865	pF
$C_{oss}$	Output Capacitance			1100	1465	pF
$C_{rss}$	Reverse Transfer Capacitance			115	170	pF
$R_g$	Gate Resistance			0.8	2.2	$\Omega$

**Switching Characteristics**

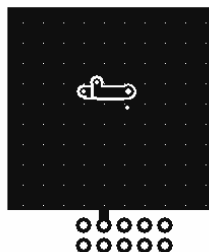
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$ , $I_D = 18.8\text{ A}$ $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		15	27	ns
$t_r$	Rise Time			7	14	ns
$t_{d(off)}$	Turn-Off Delay Time			37	59	ns
$t_f$	Fall Time			6	12	ns
$Q_{g(TOT)}$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $10\text{ V}$	$V_{DD} = 15\text{ V}$ $I_D = 18.8\text{ A}$	55	76	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\text{ V}$ to $4.5\text{ V}$		25	34	nC
$Q_{gs}$	Gate to Source Charge			12		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			6		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 18.8\text{ A}$ (Note 2)		0.83	1.2	V
		$V_{GS} = 0\text{ V}$ , $I_S = 1.9\text{ A}$ (Note 2)		0.71	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 18.8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		41	65	ns
$Q_{rr}$	Reverse Recovery Charge			20	35	nC

**NOTES:**

1.  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a. 53  $^{\circ}\text{C}/\text{W}$  when mounted on  
a 1 in<sup>2</sup> pad of 2 oz copper



b. 125  $^{\circ}\text{C}/\text{W}$  when mounted on  
a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0 %.

3.  $E_{AS}$  of 188 mJ is based on starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 1\text{ mH}$ ,  $I_{AS} = 19.4\text{ A}$ ,  $V_{DD} = 27\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

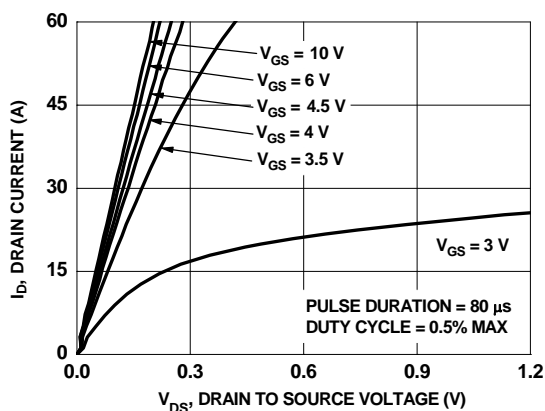


Figure 1. On Region Characteristics

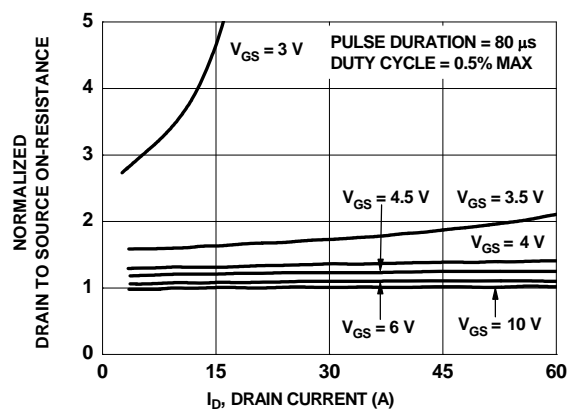


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

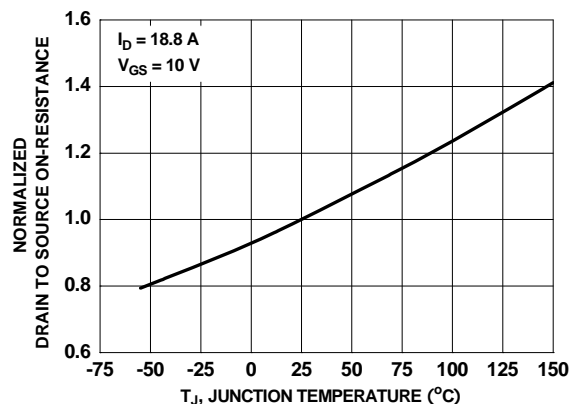


Figure 3. Normalized On Resistance vs. Junction Temperature

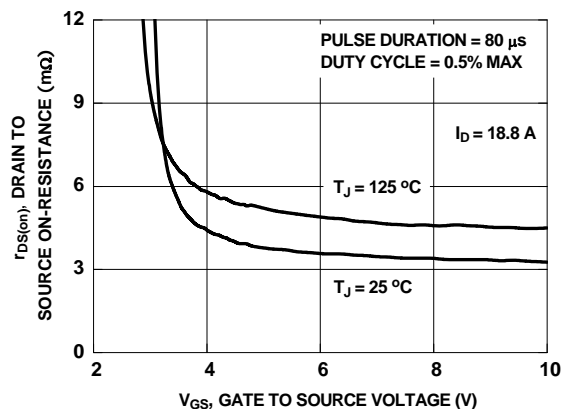


Figure 4. On-Resistance vs. Gate to Source Voltage

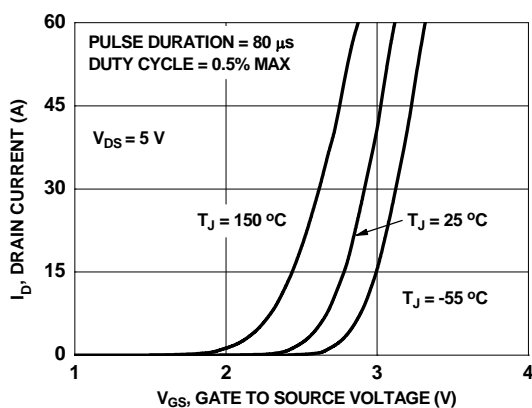


Figure 5. Transfer Characteristics

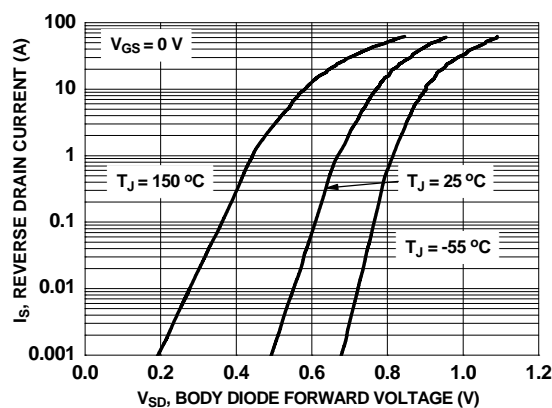


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

## Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

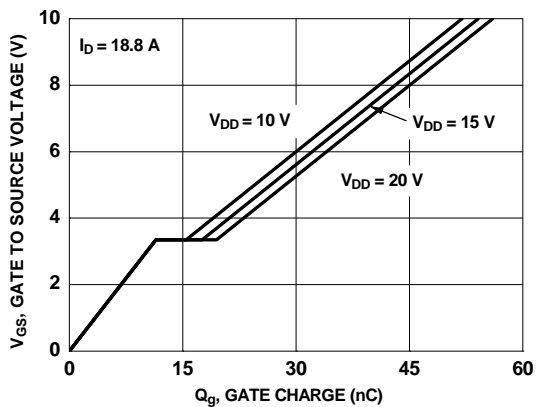


Figure 7. Gate Charge Characteristics

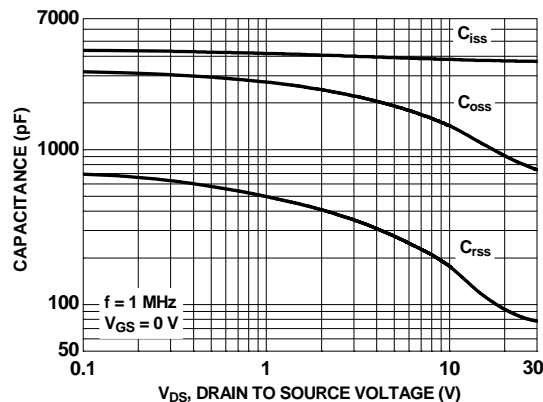


Figure 8. Capacitance vs. Drain to Source Voltage

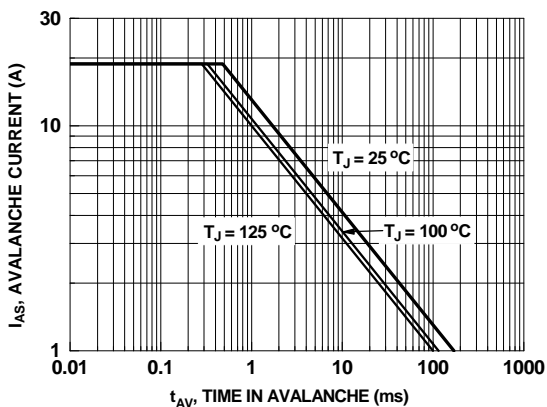


Figure 9. Unclamped Inductive Switching Capability

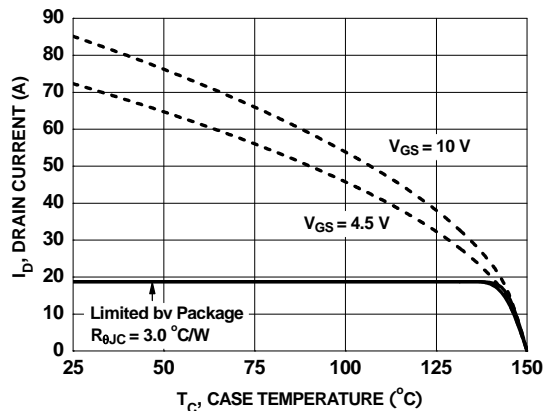


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

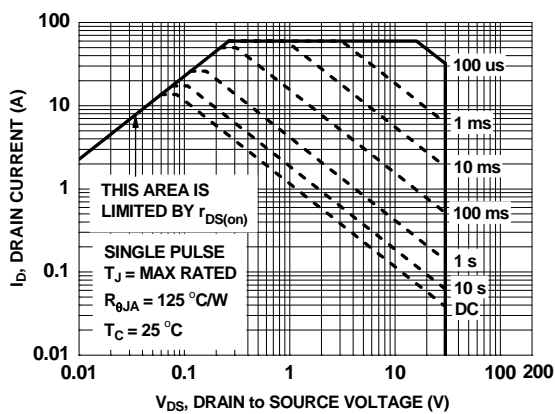


Figure 11. Forward Bias Safe Operating Area

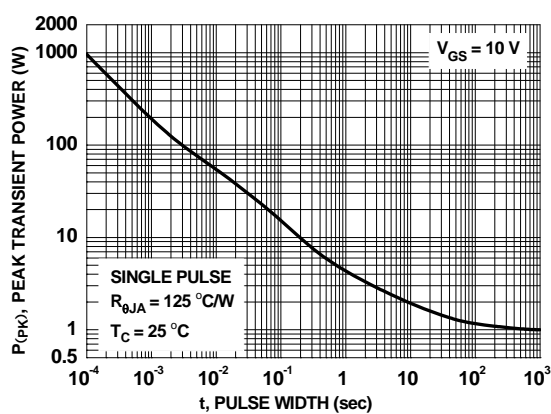


Figure 12. Single Pulse Maximum Power Dissipation

# Typical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted

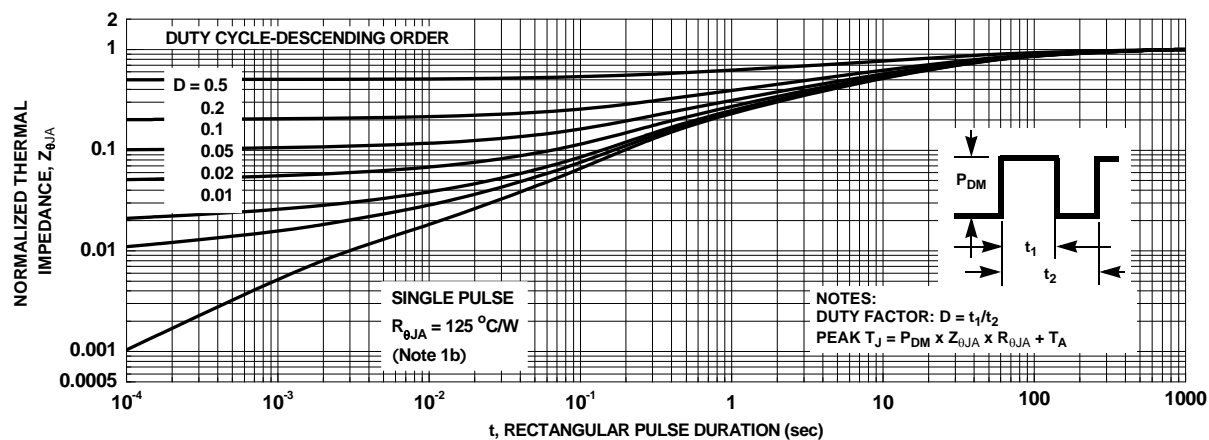
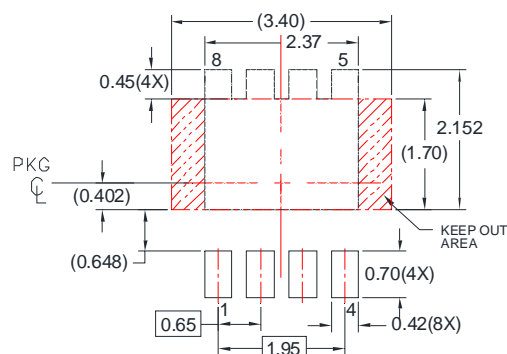
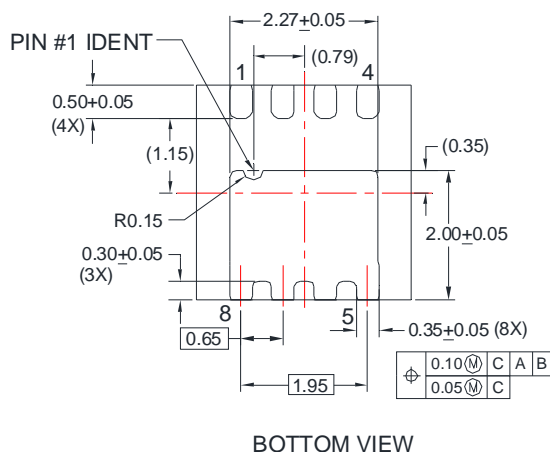
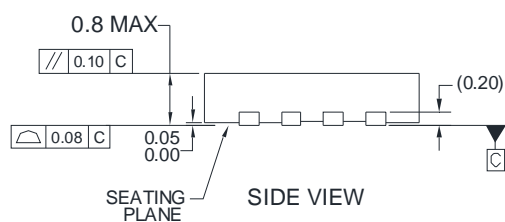
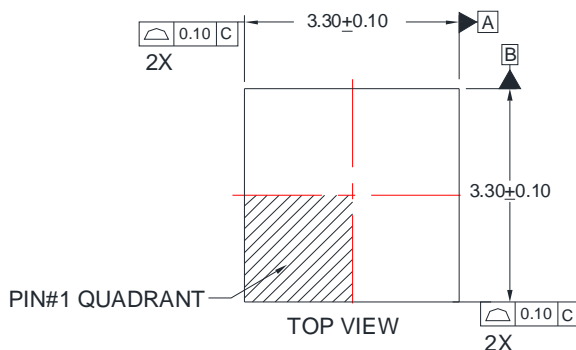


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

## Dimensional Outline and Pad Layout



### NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- D. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY
- E. DRAWING FILE NAME : MKT-MLP08Srev2
- F. FAIRCHILD SEMICONDUCTOR

